

7/17/2003

SHEET 1 OF 2

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)		ATTY. DOCKET NO. 64965-168		SERIAL NO. Divisional of Serial No. 10/015,808 10/620,605			
		APPLICANT QI XIANG					
		FILING DATE July 17, 2003		GROUP To be assigned			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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						Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
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